Final – EE486 Name_____ Spring 2016

There are 7 problems on 6 pages, plus a page of tables/plots. Show all your work. Use back of page if needed.

1.

(a) What would be the oxidation rate for a 50 nm thick oxide growing on <100> Si at 1000°C in dry O₂? (12)

(b) Is the rate limited primarily by diffusion or interface reaction? Explain. (8)

- 2. A phosphorus implant and 1st anneal result in a dose of 1×10^{14} cm⁻² and a roughly Gaussian profile with peak concentration of 3×10^{19} cm⁻³ at a depth of 50 nm.
 - (a) Assuming that the initial anneal was sufficient to complete TED and that the intrinsic diffusivity can be used, what would be the final junction depth after an additional diffusion at 1000C for 2 min for a uniform background boron doping of 10¹⁷ cm⁻³. (18)

(b) By what factor would the P diffusivity actually be changed due to non-intrinsic/E-field effects near the peak of the doping profile at the start of the 2nd anneal? (12)

- 3. Arsenic is implanted at 80 keV to a dose of 2×10^{14} cm⁻² into Si capped by 20nm of SiO₂.
 - (a) If 1 nm of oxide can be considered equivalent to 1.25 nm of Si for these implant conditions, what fraction of the dose would penetrate into the Si and at what depth into Si is resulting peak doping? (18)

(b) Using a 2+ model and neglecting any amorphization, what would be the effective Dt resulting from annealing this implant at 1100C just long enough to dissolve all the 311 defects. (12)

4. Write an expression (integral form is OK) for the ratio of film deposition rate due to sputtering as a function of sidewall angle relative to rate on a flat surface? Assume low pressure and thus no significant scattering in gas/plasma. (16)

5. A reactive ion etching process can be described by the following etch rate expression:

Rate =
$$\frac{1}{N} \left[0.1S_C F_C + \frac{1}{\frac{1}{S_C F_C} + \frac{1}{K_i F_i}} \right]$$

where the first term represents chemical etching without ion enhancement. What is the maximum anisotropy factor that can be achieved via this process and what is the associated requirement for the ion flux (F_i)? Assume that the ion flux is directed vertically (normal to wafer) and that the chemical flux is nearly isotropic even in features due to low sticking probability. Sketch the resulting etch profile. (20)

6. Describe a process to generate a 50 nm wide Cu wire surrounded by SiO₂ that does not involve etching Cu. (12)

7. Describe briefly 2 approaches for generating features smaller than half the wavelength of light source available for photolithography. (12)

	Si	В	In	As	Sb	Р
D ⁰ .0	560	0.05	0.6	0.011	0.214	3.85
D ⁰ .E	4.76	3.5	3.5	3.44	3.65	3.66
D+.0		0.95	0.6			
D+.E		3.5	3.5			
D0				31.0	15.0	4.44
DE				4.15	4.08	4.0
D=.0						44.2
D=.E						4.37

 \mathbf{f}_{I} fv Silicon 0.4 0.6 Boron 1.0 0 Phosphorus 0.98 0.02 0.6 Arsenic 0.4 Antimony 0.02 0.98 $d_I C_I^* = 5 \times 10^{25}$ exp(-4.88 eV/kT) cm⁻¹s⁻¹

$$n_i^2 = BT^3 \exp\left(-\frac{E_G}{kT}\right)$$

 $E_G = 1.12 \text{ eV}; B_{\text{Si}} = 2.23 \times 10^{31} \text{ K}^{-3} \text{ cm}^{-6}$



<111> Si	В	B/A		
Dry O ₂	$C_1 = 7.72 \text{ x } 10^2$ $\mu^2 \text{ hr}^{-1}$ $E_1 = 1.23 \text{ eV}$	$C_2 = 6.23 \text{ x } 10^6 \\ \mu \text{ hr}^{-1} \\ E_2 = 2.0 \text{ eV}$		
H ₂ O	$C_1 = 3.86 \text{ x } 10^2$ $\mu^2 \text{ hr}^{-1}$ $E_1 = 0.78 \text{ eV}$	$C_2 = 1.63 \text{ x } 10^8$ $\mu \text{ hr}^{-1}$ $E_2 = 2.05 \text{ eV}$		



Average Oxidation Rate (dx/dt) (microns/hr)

Doping concentration [cm-3]

